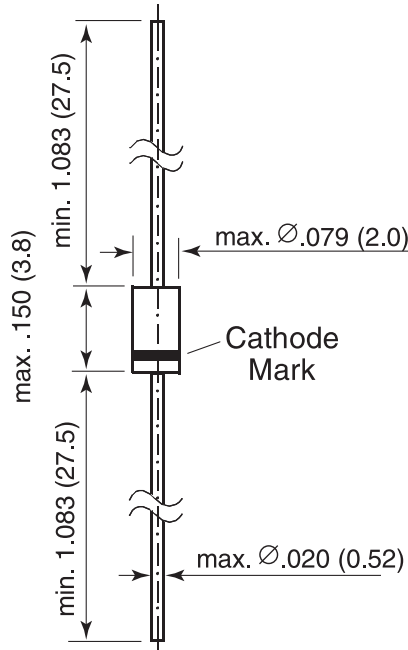




Zener Diodes

V_z Range 1.0, 2.7 to 75V
Power Dissipation 500mW

DO-204AH (DO-35 Glass)



Dimensions in inches and (millimeters)

Features

- Silicon Planar Zener Diodes.
- The Zener voltages are graded according to the international E 12 standard. Offered with either 5% or 2% tolerance. Smaller voltage tolerances and other Zener voltages are available upon request.
- These diodes are also available in MiniMELF case with the type designation ZMM1 ... ZMM75.

Mechanical Data

Case: DO-35 Glass Case

Weight: approx. 0.13g

Packaging codes/options:

D7/10K per 13" reel, (52mm tape), 20K/box

D8/10K per Ammo tape (52mm tape), 20K/box

Maximum Ratings and Thermal Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Zener Current (see Table "Characteristics")			
Power Dissipation at T _{amb} = 25°C	P _{tot}	500 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	300 ⁽²⁾	°C/W
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _S	-55 to +175	°C

Notes:

- (1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature
 (2) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

ZPD1 thru ZPD75

Vishay Semiconductors
formerly General Semiconductor



Electrical Characteristics (T_A = 25°C unless otherwise noted)

Type add suffix SB14686 for 2% tol.	Dynamic Resistance		Temperature Coefficient of Zener Voltage at I _Z = 5 mA		Reverse Voltage at I _R = 100 nA V _R (V)	Admissible Zener current ⁽²⁾	
	at I _Z = 5 mA	at I _Z = 1 mA	α _{VZ} (10 ⁻⁴ /°C)			at T _{amb} = 45°C	at T _{amb} = 25°C
	f = 1 kHz r _{Zj} (Ω)	f = 1 kHz r _{Zj} (Ω)	min	max		I _Z (mA)	I _Z (mA)
ZPD1 ⁽³⁾	6.5 (< 8)	< 50	-26	-23	-	280	340
ZPD2.7	75 (< 83)	< 500	-9	-4	-	135	160
ZPD3	80 (< 95)	< 500	-9	-3	-	117	140
ZPD3.3	80 (< 95)	< 500	-8	-3	-	109	130
ZPD3.6	80 (< 95)	< 500	-8	-3	-	101	120
ZPD3.9	80 (< 95)	< 500	-7	-3	-	92	110
ZPD4.3	80 (< 95)	< 500	-6	-1	-	85	100
ZPD4.7	70 (< 78)	< 500	-5	+2	-	76	90
ZPD5.1	30 (< 60)	< 480	-3	+4	> 0.8	67	80
ZPD5.6	10 (< 40)	< 400	-2	+6	> 1	59	70
ZPD6.2	4.8 (< 10)	< 200	-1	+7	> 2	54	64
ZPD6.8	4.5 (< 8)	< 150	+2	+7	> 3	49	58
ZPD7.5	4 (< 7)	< 50	+3	+7	> 5	44	53
ZPD8.2	4.5 (< 7)	< 50	+4	+7	> 6	40	47
ZPD9.1	4.8 (< 10)	< 50	+5	+8	> 7	36	43
ZPD10	5.2 (< 15)	< 70	+5	+8	> 7.5	33	40
ZPD11	6 (< 20)	< 70	+5	+9	> 8.5	30	36
ZPD12	7 (< 20)	< 90	+6	+9	> 9	28	32
ZPD13	9 (< 25)	< 110	+7	+9	> 10	25	29
ZPD15	11 (< 30)	< 110	+7	+9	> 11	23	27
ZPD16	13 (< 40)	< 170	+8	+9.5	> 12	20	24
ZPD18	18 (< 50)	< 170	+8	+9.5	> 14	18	21
ZPD20	20 (< 50)	< 220	+8	+10	> 15	17	20
ZPD22	25 (< 55)	< 220	+8	+10	> 17	16	18
ZPD24	28 (< 80)	< 220	+8	+10	> 18	13	16
ZPD27	30 (< 80)	< 250	+8	+10	> 20	12	14
ZPD30	35 (< 80)	< 250	+8	+10	> 22.5	10	13
ZPD33	40 (< 80)	< 250	+8	+10	> 25	9	12
ZPD36	40 (< 90)	< 250	+8	+10	> 27	9	11
ZPD39	50 (< 90)	< 300	+10	+12	> 29	8	10
ZPD43	60 (< 100)	< 700	+10	+12	> 32	7	9.2
ZPD47	70 (< 100)	< 750	+10	+12	> 35	6	8.5
ZPD51	70 (< 100)	< 750	+10	+12	> 38	6	7.8
ZPD56	< 135 ⁽⁴⁾	< 1000 ⁽⁵⁾	typ. +10 ⁽⁴⁾		> 42	5.2	7.1
ZPD62	< 150 ⁽⁴⁾	< 1000 ⁽⁵⁾	typ. +10 ⁽⁴⁾		> 47	4.8	6.4
ZPD68	< 200 ⁽⁴⁾	< 1000 ⁽⁵⁾	typ. +10 ⁽⁴⁾		> 51	4.1	5.8
ZPD75	< 250 ⁽⁴⁾	< 1500 ⁽⁵⁾	typ. +10 ⁽⁴⁾		> 55	3.9	5.3

Notes: (1) Tested with pulses t_p = 5ms

(2) Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature

(3) The ZPD1 is a silicon diode operated in forward direction. Hence, the subscript of all parameters should be "F" instead of "Z".

Connect the cathode terminal to the negative pole

(4) at I_Z = 2.5mA

(5) at I_Z = 0.5mA



Electrical Characteristics (T_A = 25°C unless otherwise noted)

Type ± 5% Tol.	Zener Voltage range ⁽¹⁾ at I _Z V _Z (V)		Test Current I _Z (mA)
	min.	max.	
ZPD1 ⁽³⁾	0.70	0.80	5.0
ZPD2.7	2.50	2.90	5.0
ZPD3	2.80	3.20	5.0
ZPD3.3	3.10	3.50	5.0
ZPD3.6	3.40	3.80	5.0
ZPD3.9	3.70	4.10	5.0
ZPD4.3	4.00	4.60	5.0
ZPD4.7	4.40	5.00	5.0
ZPD5.1	4.80	5.40	5.0
ZPD5.6	5.20	6.00	5.0
ZPD6.2	5.80	6.60	5.0
ZPD6.8	6.40	7.20	5.0
ZPD7.5	7.00	7.90	5.0
ZPD8.2	7.70	8.70	5.0
ZPD9.1	8.50	9.60	5.0
ZPD10	9.40	10.6	5.0
ZPD11	10.4	11.6	5.0
ZPD12	11.4	12.7	5.0
ZPD13	12.4	14.1	5.0
ZPD15	13.8	15.6	5.0
ZPD16	15.3	17.1	5.0
ZPD18	16.8	19.1	5.0
ZPD20	18.8	21.2	5.0
ZPD22	20.8	23.3	5.0
ZPD24	22.8	25.6	5.0
ZPD27	25.1	28.9	5.0
ZPD30	28.0	32.0	5.0
ZPD33	31.0	35.0	5.0
ZPD36	34.0	38.0	5.0
ZPD39	37.0	41.0	5.0
ZPD43	40.0	46.0	5.0
ZPD47	44.0	50.0	5.0
ZPD51	48.0	54.0	5.0
ZPD56	52.0	60.0	2.5
ZPD62	58.0	66.0	2.5
ZPD68	64.0	72.0	2.5
ZPD75	70.0	79.0	2.5

Type add suffix SB14686 for ± 2% Tol.	Zener Voltage range ⁽¹⁾ at I _Z V _Z (V)		Test Current I _Z (mA)
	min.	max.	
ZPD1 ⁽³⁾	-	-	5.0
ZPD2.7	2.65	2.75	5.0
ZPD3	2.94	3.06	5.0
ZPD3.3	3.23	3.37	5.0
ZPD3.6	3.53	3.67	5.0
ZPD3.9	3.82	3.98	5.0
ZPD4.3	4.21	4.39	5.0
ZPD4.7	4.61	4.79	5.0
ZPD5.1	5.00	5.20	5.0
ZPD5.6	5.49	5.71	5.0
ZPD6.2	6.08	6.32	5.0
ZPD6.8	6.66	6.94	5.0
ZPD7.5	7.35	7.65	5.0
ZPD8.2	8.04	8.36	5.0
ZPD9.1	8.92	9.28	5.0
ZPD10	9.80	10.2	5.0
ZPD11	10.8	11.2	5.0
ZPD12	11.8	12.2	5.0
ZPD13	12.7	13.3	5.0
ZPD15	14.7	15.3	5.0
ZPD16	15.7	16.3	5.0
ZPD18	17.6	18.4	5.0
ZPD20	19.6	20.4	5.0
ZPD22	21.6	22.4	5.0
ZPD24	23.5	24.5	5.0
ZPD27	26.5	27.5	5.0
ZPD30	29.4	30.6	5.0
ZPD33	32.3	33.7	5.0
ZPD36	35.3	36.7	5.0
ZPD39	38.2	39.8	5.0
ZPD43	42.1	43.9	5.0
ZPD47	46.1	47.9	5.0
ZPD51	50.0	52.0	5.0
ZPD56	54.9	46.9	2.5
ZPD62	60.8	63.2	2.5
ZPD68	66.6	69.4	2.5
ZPD75	73.5	76.5	2.5

Notes:

(1) Measured with pulses t_p = 5 ms

(3) The ZPD1 is a silicon diode operated in forward direction. Hence, the subscript of all parameters should be "F" instead of "Z".

Connect the cathode terminal to the negative pole

ZPD1 thru ZPD75

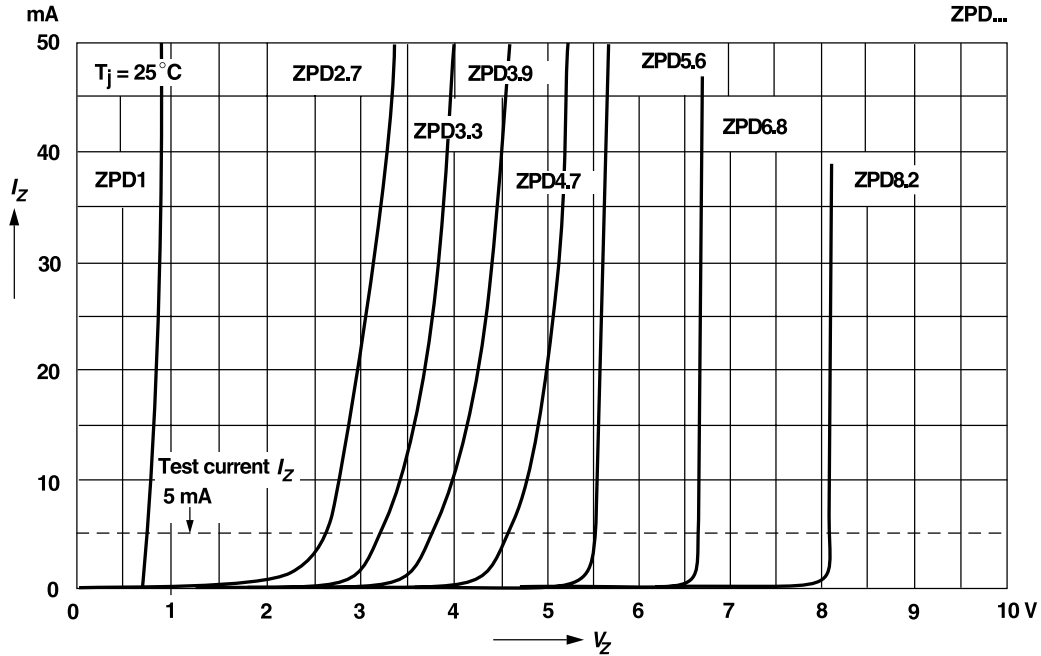
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formerly General Semiconductor



Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

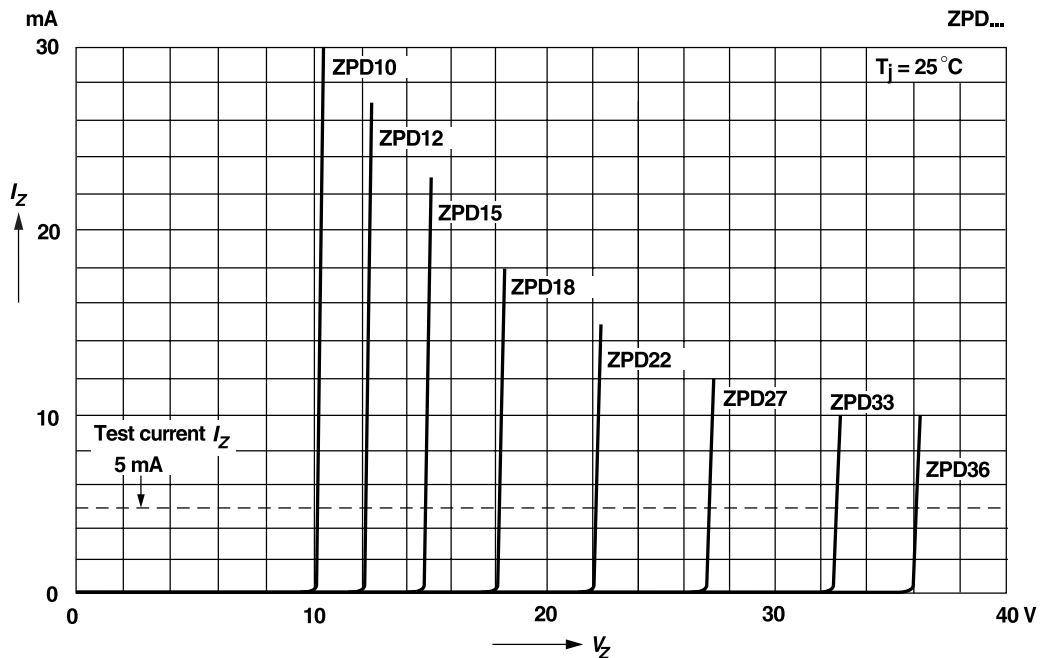
Breakdown characteristics

$T_j = \text{constant (pulsed)}$



Breakdown characteristics

$T_j = \text{constant (pulsed)}$

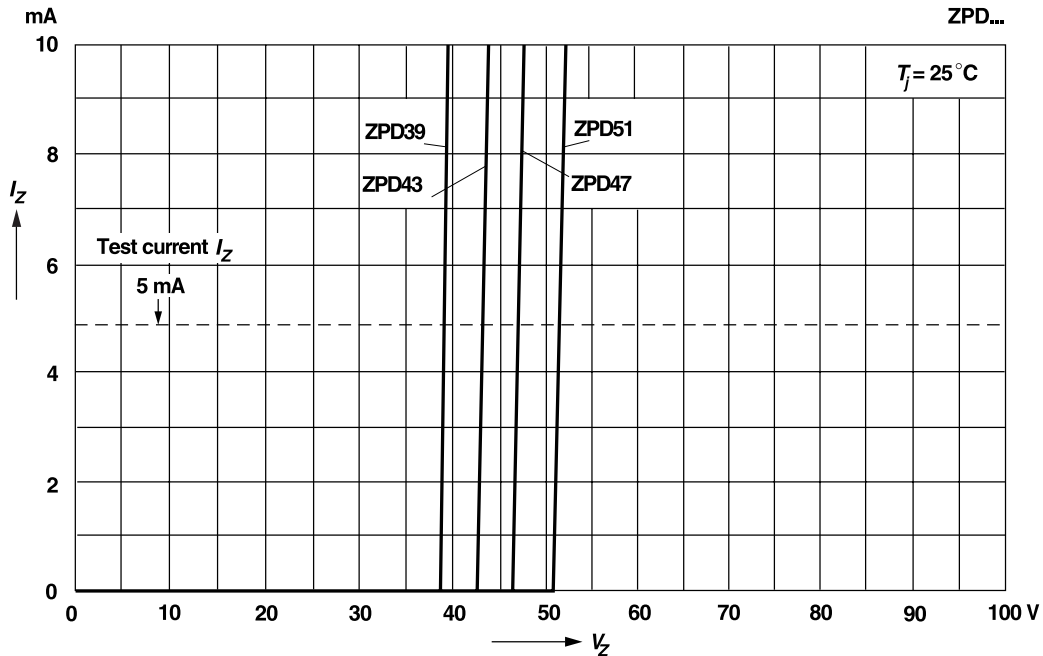




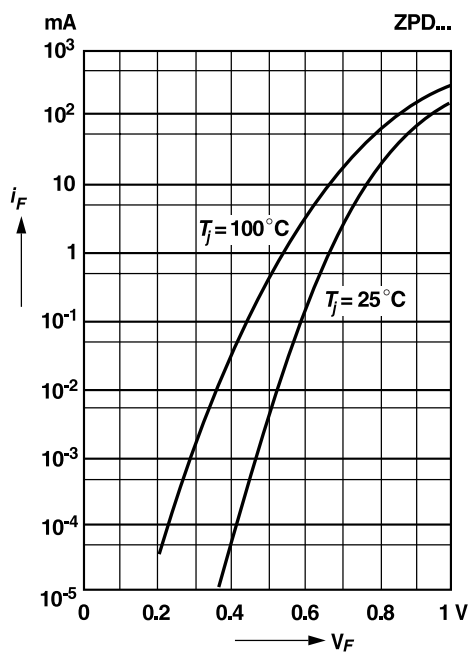
Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Breakdown characteristics

$T_j = \text{constant (pulsed)}$

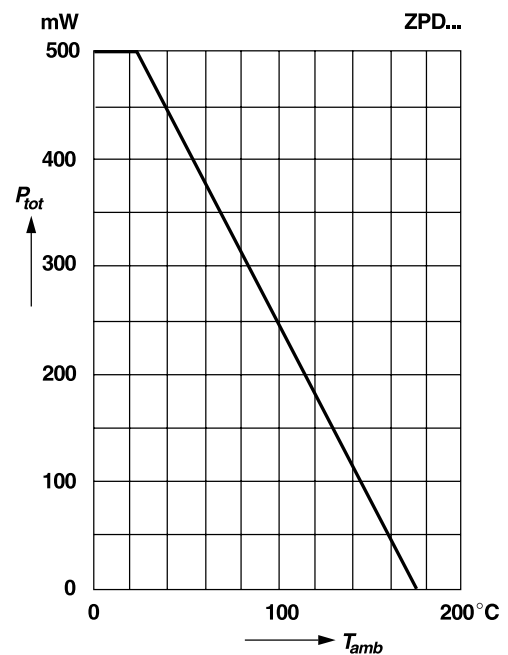


Forward characteristics



Admissible power dissipation versus ambient temperature

Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature



ZPD1 thru ZPD75

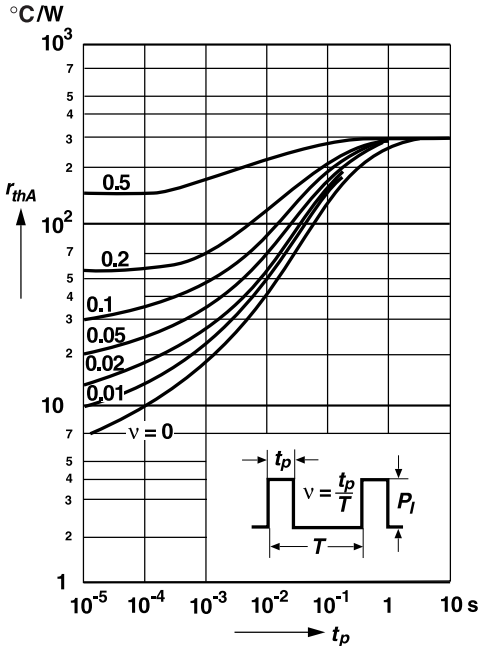


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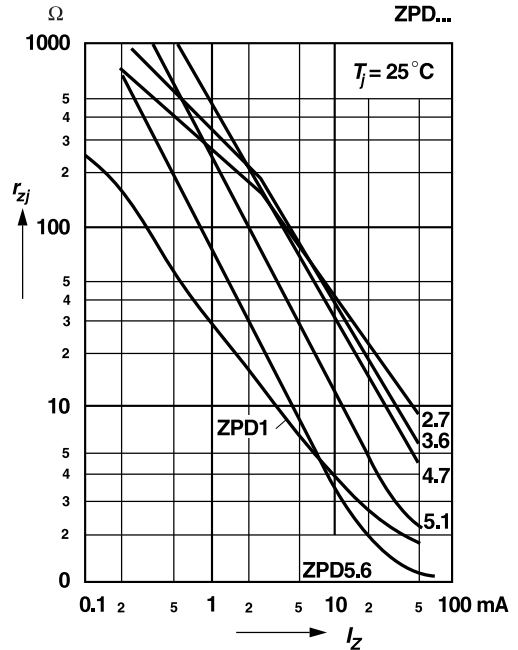
Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Pulse thermal resistance versus pulse duration

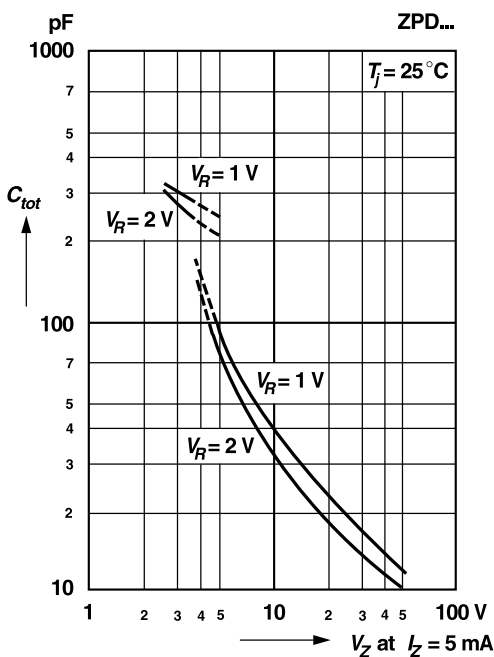
Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature



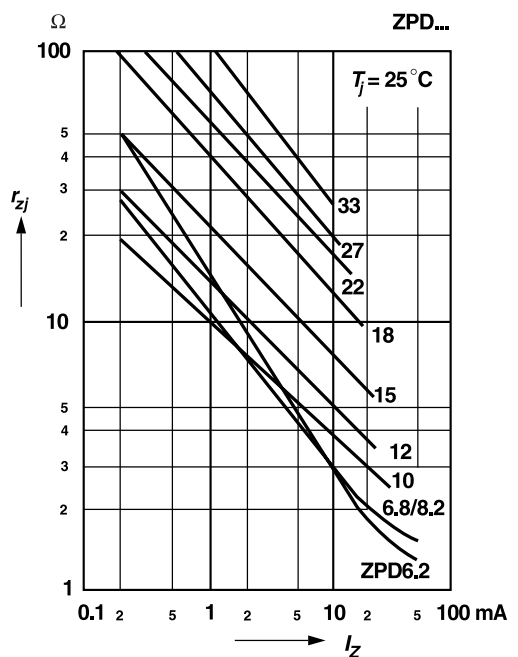
Dynamic resistance versus Zener current



Capacitance versus Zener voltage



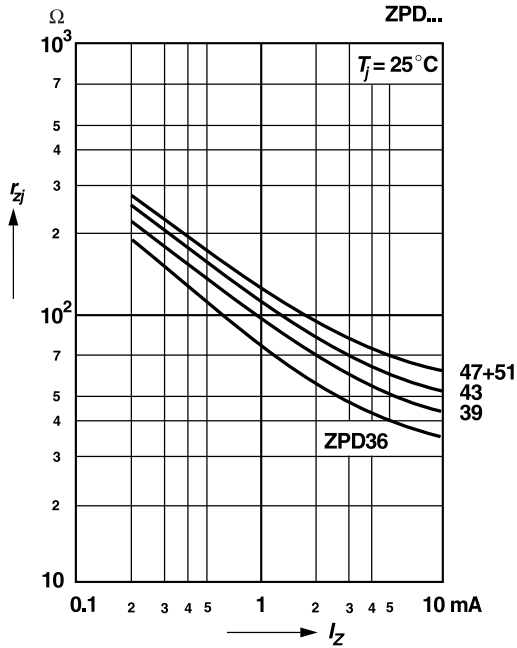
Dynamic resistance versus Zener current





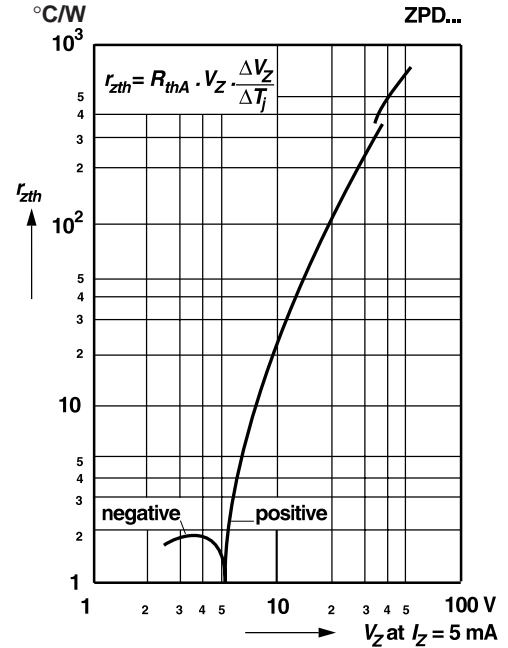
Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Dynamic resistance versus Zener current

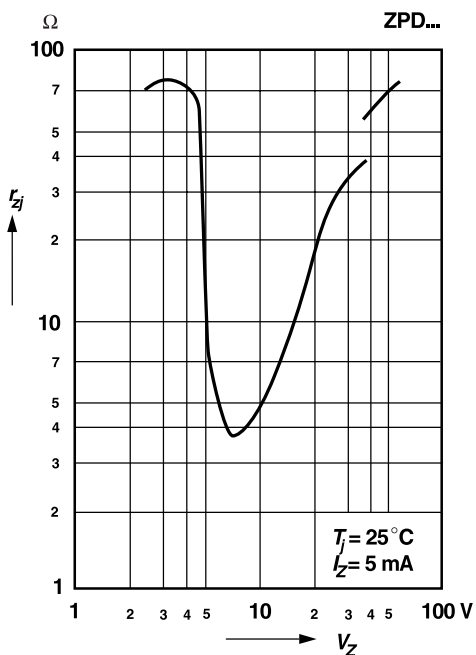


Thermal differential resistance versus Zener voltage

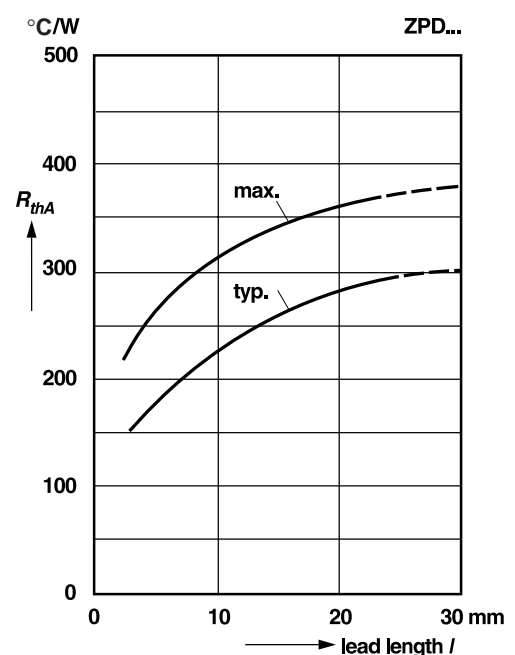
Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature



Dynamic resistance versus Zener voltage



Thermal resistance versus lead length



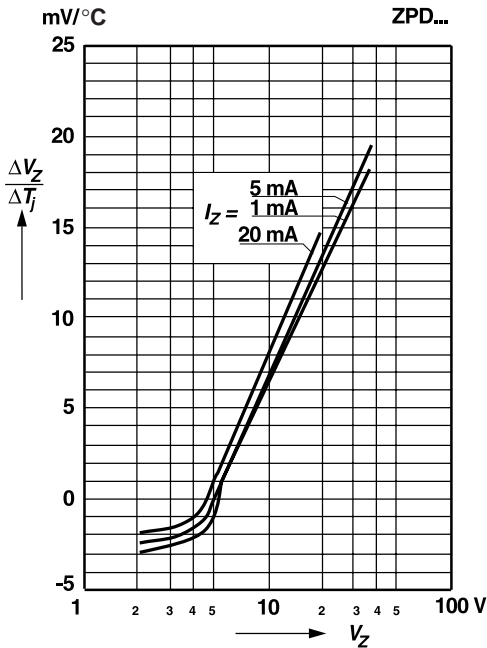
ZPD1 thru ZPD75

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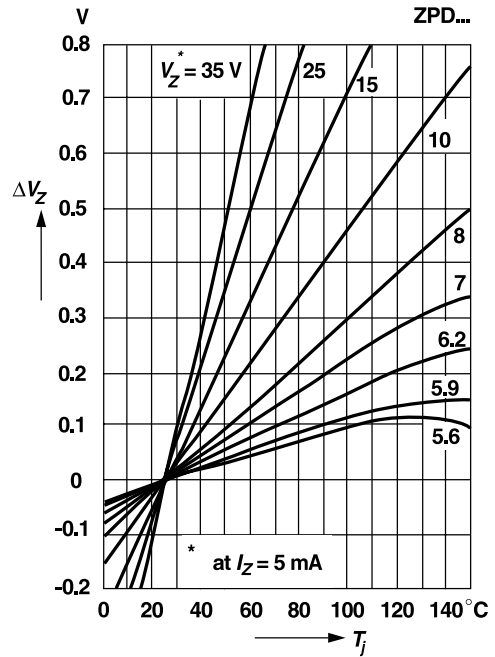


Ratings and Characteristic Curves (T_A = 25°C unless otherwise noted)

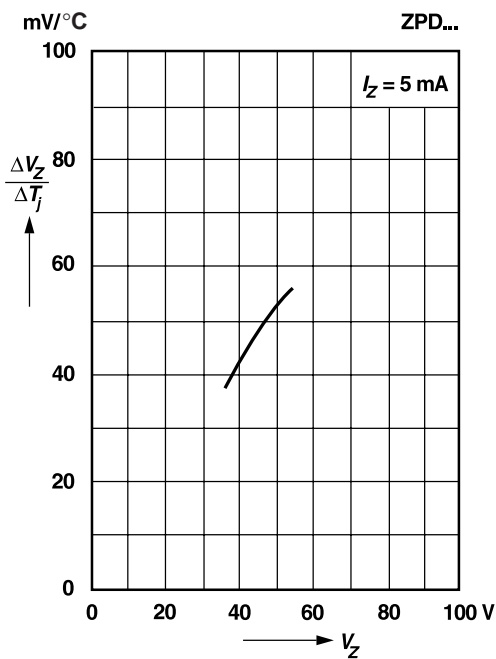
Temperature dependence of Zener voltage versus Zener voltage



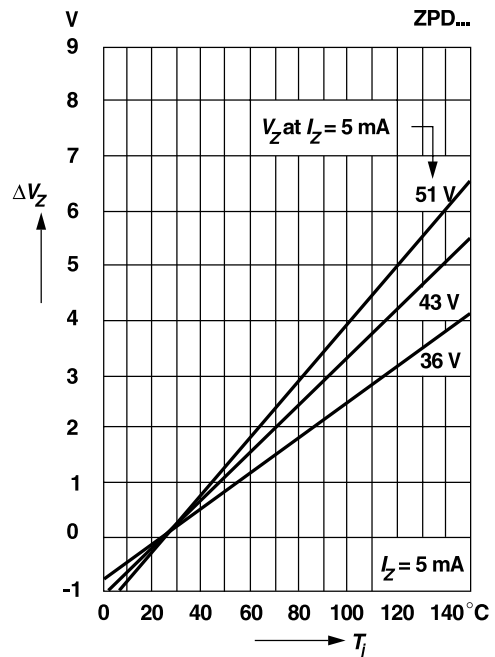
Change of Zener voltage versus junction temperature



Temperature dependence of Zener voltage versus Zener voltage



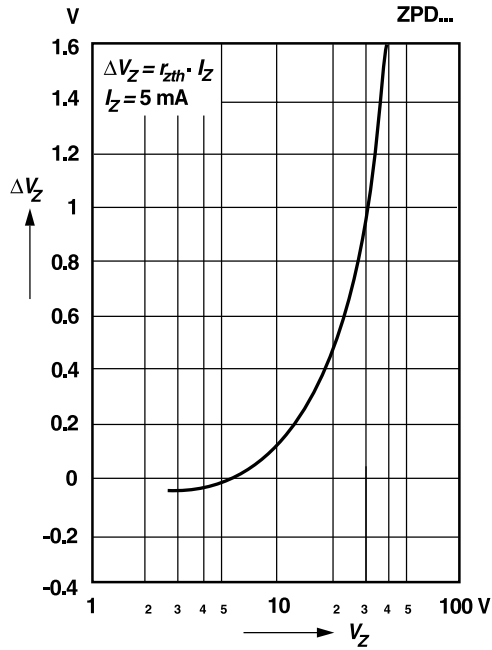
Change of Zener voltage versus junction temperature





Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage



Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage

